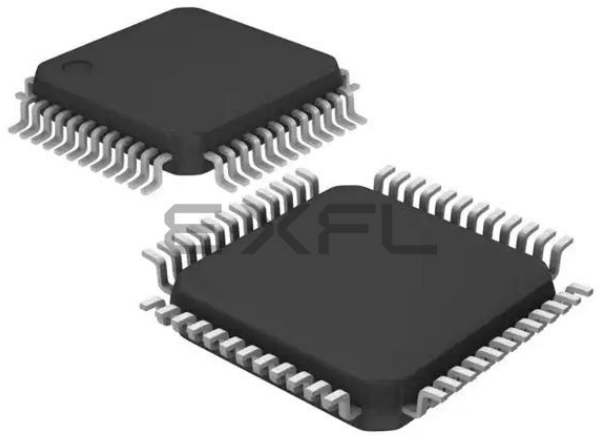
Renesas Electronics America Inc - R5F104GFDFB#V0 Datasheet



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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I²C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	34
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LFQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104gfdfb-v0

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Pin count	Package	Fields of Application Note	Ordering Part Number
48 pins	48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)	A	R5F104GAAFB#V0, R5F104GCAFB#V0, R5F104GDAFB#V0, R5F104GEAFB#V0, R5F104GFAFB#V0, R5F104GGAFB#V0, R5F104GHAFB#V0, R5F104GJAFB#V0 R5F104GAAFB#X0, R5F104GCAFB#X0, R5F104GDAFB#X0, R5F104GEAFB#X0, R5F104GFAFB#X0, R5F104GGAFB#X0, R5F104GHAFB#X0, R5F104GJAFB#X0 R5F104GKAFB#30, R5F104GLAFB#30 R5F104GKAFB#50, R5F104GLAFB#50
		D	R5F104GADFB#V0, R5F104GCDFB#V0, R5F104GDDFB#V0, R5F104GEDFB#V0, R5F104GFDFB#V0, R5F104GGDFB#V0, R5F104GHDFB#V0, R5F104GJDFB#V0 R5F104GADFB#X0, R5F104GCDFB#X0, R5F104GDDFB#X0, R5F104GEDFB#X0, R5F104GFDFB#X0, R5F104GGDFB#X0, R5F104GHDFB#X0, R5F104GJDFB#X0
		G	R5F104GAGFB#V0, R5F104GCGFB#V0, R5F104GDGFB#V0, R5F104GEGFB#V0, R5F104GFGFB#V0, R5F104GGGFB#V0, R5F104GHGFB#V0, R5F104GJGFB#V0 R5F104GAGFB#X0, R5F104GCGFB#X0, R5F104GDGFB#X0, R5F104GEGFB#X0, R5F104GFGFB#X0, R5F104GGGFB#X0, R5F104GHGFB#X0, R5F104GJGFB#X0 R5F104GKGFB#30, R5F104GLGFB#30 R5F104GKGFB#50, R5F104GLGFB#50
	48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)	A	R5F104GAANA#U0, R5F104GCANA#U0, R5F104GDANA#U0, R5F104GEANA#U0, R5F104GFANA#U0, R5F104GGANA#U0, R5F104GHANA#U0, R5F104GJANA#U0 R5F104GAANA#W0, R5F104GCANA#W0, R5F104GDANA#W0, R5F104GEANA#W0, R5F104GFANA#W0, R5F104GGANA#W0, R5F104GHANA#W0, R5F104GJANA#W0 R5F104GKANA#U0, R5F104GLANA#U0 R5F104GKANA#W0, R5F104GLANA#W0
		D	R5F104GADNA#U0, R5F104GCDNA#U0, R5F104GDDNA#U0, R5F104GEDNA#U0, R5F104GFDNA#U0, R5F104GGDNA#U0, R5F104GHDNA#U0, R5F104GJDNA#U0 R5F104GADNA#W0, R5F104GCDNA#W0, R5F104GDDNA#W0, R5F104GEDNA#W0, R5F104GFDNA#W0, R5F104GGDNA#W0, R5F104GHDNA#W0, R5F104GJDNA#W0
		G	R5F104GAGNA#U0, R5F104GCGNA#U0, R5F104GDGNA#U0, R5F104GEGNA#U0, R5F104GFGNA#U0, R5F104GGGNA#U0, R5F104GHGNA#U0, R5F104GJGNA#U0 R5F104GAGNA#W0, R5F104GCGNA#W0, R5F104GDGNA#W0, R5F104GEGNA#W0, R5F104GFGNA#W0, R5F104GGGNA#W0, R5F104GHGNA#W0, R5F104GJGNA#W0 R5F104GKGNA#U0, R5F104GLGNA#U0 R5F104GKGNA#W0, R5F104GLGNA#W0
52 pins	52-pin plastic LQFP (10 × 10 mm, 0.65 mm pitch)	A	R5F104JCAFA#V0, R5F104JDAFA#V0, R5F104JEAFA#V0, R5F104JFAFA#V0, R5F104JGAFA#V0, R5F104JHAFA#V0, R5F104JJAFA#V0 R5F104JCAFA#X0, R5F104JDAFA#X0, R5F104JEAFA#X0, R5F104JFAFA#X0, R5F104JGAFA#X0, R5F104JHAFA#X0, R5F104JJAFA#X0
		D	R5F104JCDFA#V0, R5F104JDDFA#V0, R5F104JEDFA#V0, R5F104JFDFA#V0, R5F104JGDFA#V0, R5F104JHDFA#V0, R5F104JJDFA#V0 R5F104JCDFA#X0, R5F104JDDFA#X0, R5F104JEDFA#X0, R5F104JFDFA#X0, R5F104JGDFA#X0, R5F104JHDFA#X0, R5F104JJDFA#X0
		G	R5F104JCGFA#V0, R5F104JDGFA#V0, R5F104JEGFA#V0, R5F104JFGFA#V0, R5F104JGGFA#V0, R5F104JHGFA#V0, R5F104JJGFA#V0 R5F104JCGFA#X0, R5F104JDGFA#X0, R5F104JEGFA#X0, R5F104JFGFA#X0, R5F104JGGFA#X0, R5F104JHGFA#X0, R5F104JJGFA#X0

Note For the fields of application, refer to **Figure 1 - 1 Part Number, Memory Size, and Package of RL78/G14**.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.
R5F104xD (x = A to C, E to G, J, L): Start address FE900H
R5F104xE (x = A to C, E to G, J, L): Start address FE900H
For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.
The target products and start address of the RAM areas used by the flash library are shown below.
R5F104xJ (x = F, G, J, L, M, P): Start address F9F00H
For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

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Item		80-pin R5F104Mx (x = F to H, J)	100-pin R5F104Px (x = F to H, J)
Clock output/buzzer output		2	2
		• 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) • 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation)	
8/10-bit resolution A/D converter		17 channels	20 channels
D/A converter		2 channels	2 channels
Comparator		2 channels	2 channels
Serial interface		[80-pin, 100-pin products] • CSI: 2 channels/UART (UART supporting LIN-bus): 1 channel/simplified I^2C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I^2C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I^2C: 2 channels • CSI: 2 channels/UART: 1 channel/simplified I^2C: 2 channels	
	I^2C bus	2 channels	2 channels
Data transfer controller (DTC)		39 sources	39 sources
Event link controller (ELC)		Event input: 26 Event trigger output: 9	
Vectored interrupt sources	Internal	32	32
	External	13	13
Key interrupt		8	8
Reset		• Reset by $\overline{\text{RESET}}$ pin • Internal reset by watchdog timer • Internal reset by power-on-reset • Internal reset by voltage detector • Internal reset by illegal instruction execution Note • Internal reset by RAM parity error • Internal reset by illegal-memory access	
Power-on-reset circuit		• Power-on-reset: 1.51 ±0.04 V (T_A = –40 to +85°C) 1.51 ±0.06 V (T_A = –40 to +105°C) • Power-down-reset: 1.50 ±0.04 V (T_A = –40 to +85°C) 1.50 ±0.06 V (T_A = –40 to +105°C)	
Voltage detector		1.63 V to 4.06 V (14 stages)	
On-chip debug function		Provided	
Power supply voltage		V_{DD} = 1.6 to 5.5 V (T_A = -40 to +85°C) V_{DD} = 2.4 to 5.5 V (T_A = -40 to +105°C)	
Operating ambient temperature		T_A = -40 to +85°C (A: Consumer applications, D: Industrial applications), T_A = -40 to +105°C (G: Industrial applications)	

Note The illegal instruction is generated when instruction code FFH is executed.
Reset by the illegal instruction execution is not issued by emulation with the in-circuit emulator or on-chip debug emulator.

Note 1. Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 3. When high-speed system clock and subsystem clock are stopped.

Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.

Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz
2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (64 MHz max.)

Remark 3. f_{IH}: High-speed on-chip oscillator clock frequency (32 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(3) Flash ROM: 384 to 512 KB of 48- to 100-pin products

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions					MIN.	TYP.	MAX.	Unit
Supply current Note 1	I_{DD1}	Operating mode	HS (high-speed main) mode Note 5	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 3	Basic operation	V_{DD} = 5.0 V		2.9		mA
						V_{DD} = 3.0 V		2.9		
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 3	Basic operation	V_{DD} = 5.0 V		2.5		
						V_{DD} = 3.0 V		2.5		
			HS (high-speed main) mode Note 5	f_{HOCO} = 64 MHz, f_{IH} = 32 MHz Note 3	Normal operation	V_{DD} = 5.0 V		6.0	11.2	mA
						V_{DD} = 3.0 V		6.0	11.2	
				f_{HOCO} = 32 MHz, f_{IH} = 32 MHz Note 3	Normal operation	V_{DD} = 5.0 V		5.5	10.6	
						V_{DD} = 3.0 V		5.5	10.6	
				f_{HOCO} = 48 MHz, f_{IH} = 24 MHz Note 3	Normal operation	V_{DD} = 5.0 V		4.7	8.6	
						V_{DD} = 3.0 V		4.7	8.6	
				f_{HOCO} = 24 MHz, f_{IH} = 24 MHz Note 3	Normal operation	V_{DD} = 5.0 V		4.4	8.2	
						V_{DD} = 3.0 V		4.4	8.2	
				f_{HOCO} = 16 MHz, f_{IH} = 16 MHz Note 3	Normal operation	V_{DD} = 5.0 V		3.3	5.9	
						V_{DD} = 3.0 V		3.3	5.9	
			LS (low-speed main) mode Note 5	f_{HOCO} = 8 MHz, f_{IH} = 8 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.5	2.5	mA
						V_{DD} = 2.0 V		1.5	2.5	
			LV (low-voltage main) mode Note 5	f_{HOCO} = 4 MHz, f_{IH} = 4 MHz Note 3	Normal operation	V_{DD} = 3.0 V		1.5	2.1	mA
						V_{DD} = 2.0 V		1.5	2.1	
			HS (high-speed main) mode Note 5	f_{MX} = 20 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		3.7	6.8	mA
						Resonator connection		3.9	7.0	
				f_{MX} = 20 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		3.7	6.8	
						Resonator connection		3.9	7.0	
				f_{MX} = 10 MHz Note 2, V_{DD} = 5.0 V	Normal operation	Square wave input		2.3	4.1	
						Resonator connection		2.3	4.2	
				f_{MX} = 10 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		2.3	4.1	
						Resonator connection		2.3	4.2	
			LS (low-speed main) mode Note 5	f_{MX} = 8 MHz Note 2, V_{DD} = 3.0 V	Normal operation	Square wave input		1.4	2.4	mA
						Resonator connection		1.4	2.5	
				f_{MX} = 8 MHz Note 2, V_{DD} = 2.0 V	Normal operation	Square wave input		1.4	2.4	
						Resonator connection		1.4	2.5	
			Subsystem clock operation	f_{SUB} = 32.768 kHz Note 4 T_A = -40°C	Normal operation	Square wave input		5.2		µA
						Resonator connection		5.2		
				f_{SUB} = 32.768 kHz Note 4 T_A = +25°C	Normal operation	Square wave input		5.3	7.7	
						Resonator connection		5.3	7.7	
				f_{SUB} = 32.768 kHz Note 4 T_A = +50°C	Normal operation	Square wave input		5.5	10.6	
						Resonator connection		5.5	10.6	
				f_{SUB} = 32.768 kHz Note 4 T_A = +70°C	Normal operation	Square wave input		5.9	13.2	
						Resonator connection		6.0	13.2	
				f_{SUB} = 32.768 kHz Note 4 T_A = +85°C	Normal operation	Square wave input		6.8	17.5	
						Resonator connection		6.9	17.5	

(**Notes** and **Remarks** are listed on the next page.)

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) **(2/2)**

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Timer RD input high-level width, low-level width	t_{TDIH}, t_{TDIL}	TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1		3/f_{CLK}			ns
Timer RD forced cutoff signal input low-level width	t_{TDSIL}	P130/INTP0	2MHz < f_{CLK} ≤ 32 MHz	1			µs
			f_{CLK} ≤ 2 MHz	1/f_{CLK} + 1			
Timer RG input high-level width, low-level width	t_{TGIH}, t_{TGIL}	TRGIOA, TRGIOB		2.5/f_{CLK}			ns
TO00 to TO03, TO10 to TO13, TRJIO0, TRJO0, TRDIOA0, TRDIOA1, TRDIOB0, TRDIOB1, TRDIOC0, TRDIOC1, TRDIOD0, TRDIOD1, TRGIOA, TRGIOB output frequency	f_{TO}	HS (high-speed main) mode	4.0 V ≤ EV_{DD0} ≤ 5.5 V			16	MHz
			2.7 V ≤ EV_{DD0} < 4.0 V			8	MHz
			1.8 V ≤ EV_{DD0} < 2.7 V			4	MHz
			1.6 V ≤ EV_{DD0} < 1.8 V			2	MHz
		LS (low-speed main) mode	1.8 V ≤ EV_{DD0} ≤ 5.5 V			4	MHz
			1.6 V ≤ EV_{DD0} < 1.8 V			2	MHz
		LV (low-voltage main) mode	1.6 V ≤ EV_{DD0} ≤ 5.5 V			2	MHz
PCLBUZ0, PCLBUZ1 output frequency	f_{PCL}	HS (high-speed main) mode	4.0 V ≤ EV_{DD0} ≤ 5.5 V			16	MHz
			2.7 V ≤ EV_{DD0} < 4.0 V			8	MHz
			1.8 V ≤ EV_{DD0} < 2.7 V			4	MHz
			1.6 V ≤ EV_{DD0} < 1.8 V			2	MHz
		LS (low-speed main) mode	1.8 V ≤ EV_{DD0} ≤ 5.5 V			4	MHz
			1.6 V ≤ EV_{DD0} < 1.8 V			2	MHz
		LV (low-voltage main) mode	1.8 V ≤ EV_{DD0} ≤ 5.5 V			4	MHz
			1.6 V ≤ EV_{DD0} < 1.8 V			2	MHz
Interrupt input high-level width, low-level width	t_{INTH}, t_{INTL}	INTP0	1.6 V ≤ V_{DD} ≤ 5.5 V	1			µs
		INTP1 to INTP11	1.6 V ≤ EV_{DD0} ≤ 5.5 V	1			µs
Key interrupt input low-level width	t_{KR}	KR0 to KR7	1.8 V ≤ EV_{DD0} ≤ 5.5 V	250			ns
			1.6 V ≤ EV_{DD0} < 1.8 V	1			µs
$\overline{\text{RESET}}$ low-level width	t_{RSL}			10			µs

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

(T_A = -40 to +85°C, 1.6 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V) (2/2)

Parameter	Symbol	Conditions		HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		transmission	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V		Note 1		Note 1		Note 1	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 1.4 kΩ, V_b = 2.7 V		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
			2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V		Note 3		Note 3		Note 3	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 2.7 kΩ, V_b = 2.3 V		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
			1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V		Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
			Theoretical value of the maximum transfer rate C_b = 50 pF, R_b = 5.5 kΩ, V_b = 1.6 V		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps

Note 1. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD0} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.2}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 2. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to **Note 1** above to calculate the maximum transfer rate under conditions of the customer.

Note 3. The smaller maximum transfer rate derived by using f_{MCK}/6 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.7 V ≤ EV_{DD0} < 4.0 V and 2.3 V ≤ V_b ≤ 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

* This value is the theoretical value of the relative difference between the transmission and reception sides

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode)

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

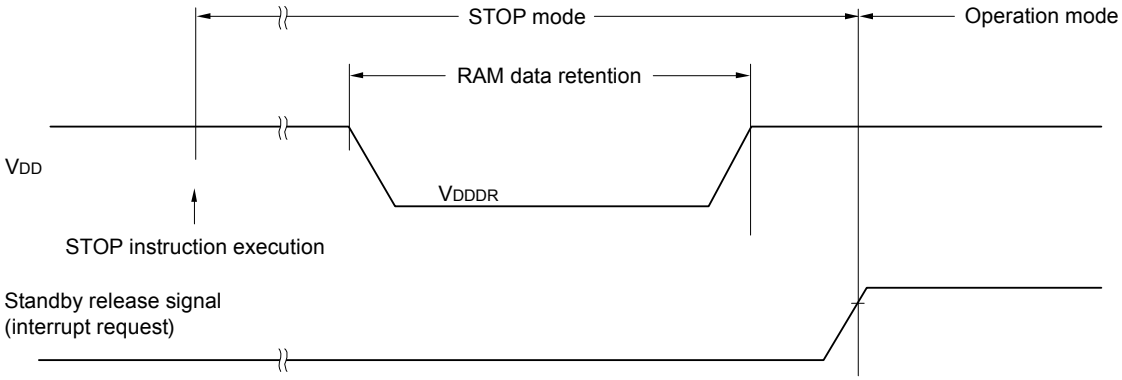
Parameter	Symbol	Conditions	HS (high-speed main) mode		LS (low-speed main) mode		LV (low-voltage main) mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	f_{SCL}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		300 Note 1		300 Note 1	kHz
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ		1000 Note 1		300 Note 1		300 Note 1	kHz
		4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ		400 Note 1		300 Note 1		300 Note 1	kHz
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ		400 Note 1		300 Note 1		300 Note 1	kHz
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	t_{LOW}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1550		1550		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	475		1550		1550		ns
		4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	1150		1550		1550		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	1150		1550		1550		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	1550		1550		1550		ns
Hold time when SCLr = "H"	t_{HIGH}	4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 50 pF, R_b = 2.7 kΩ	245		610		610		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 50 pF, R_b = 2.7 kΩ	200		610		610		ns
		4.0 V ≤ EV_{DD0} ≤ 5.5 V, 2.7 V ≤ V_b ≤ 4.0 V, C_b = 100 pF, R_b = 2.8 kΩ	675		610		610		ns
		2.7 V ≤ EV_{DD0} < 4.0 V, 2.3 V ≤ V_b ≤ 2.7 V, C_b = 100 pF, R_b = 2.7 kΩ	600		610		610		ns
		1.8 V ≤ EV_{DD0} < 3.3 V, 1.6 V ≤ V_b ≤ 2.0 V Note 2, C_b = 100 pF, R_b = 5.5 kΩ	610		610		610		ns

2.7 RAM Data Retention Characteristics

(T_A = -40 to +85°C, V_{SS} = 0V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	V_{DDDR}		1.46 Note		5.5	V

Note The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset is effected, but RAM data is not retained when a POR reset is effected.



2.8 Flash Memory Programming Characteristics

(T_A = -40 to +85°C, 1.8 V ≤ V_{DD} ≤ 5.5 V, V_{SS} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	f_{CLK}	1.8 V ≤ V_{DD} ≤ 5.5 V	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	C_{erwr}	Retained for 20 years T_A = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year T_A = 25°C		1,000,000		
		Retained for 5 years T_A = 85°C	100,000			
		Retained for 20 years T_A = 85°C	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

(T_A = -40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

Note 1. Total current flowing into V_{DD}, EV_{DD0}, and EV_{DD1}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DD0}, and EV_{DD1}, or V_{SS}, EV_{SS0}, and EV_{SS1}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.

Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.

Note 3. When high-speed system clock and subsystem clock are stopped.

Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.

Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz
2.4 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 16 MHz

Remark 1. f_{MX}: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

Remark 2. f_{HOCO}: High-speed on-chip oscillator clock frequency (64 MHz max.)

Remark 3. f_{IH}: High-speed on-chip oscillator clock frequency (32 MHz max.)

Remark 4. f_{SUB}: Subsystem clock frequency (XT1 clock oscillation frequency)

Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(4) Peripheral Functions (Common to all products)

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Low-speed on-chip oscillator operating current	I_{FIL} Note 1				0.20		µA
RTC operating current	I_{RTC} Notes 1, 2, 3				0.02		µA
12-bit interval timer operating current	I_{IT} Notes 1, 2, 4				0.02		µA
Watchdog timer operating current	I_{WDT} Notes 1, 2, 5	f_{IL} = 15 kHz			0.22		µA
A/D converter operating current	I_{ADC} Notes 1, 6	When conversion at maximum speed	Normal mode, AV_{REFP} = V_{DD} = 5.0 V		1.3	1.7	mA
			Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	I_{ADREF} Note 1				75.0		µA
Temperature sensor operating current	I_{TMPS} Note 1				75.0		µA
D/A converter operating current	I_{DAC} Notes 1, 11, 13	Per D/A converter channel				1.5	mA
Comparator operating current	I_{CMP} Notes 1, 12, 13	V_{DD} = 5.0 V, Regulator output voltage = 2.1 V	Window mode		12.5		µA
			Comparator high-speed mode		6.5		µA
			Comparator low-speed mode		1.7		µA
		V_{DD} = 5.0 V, Regulator output voltage = 1.8 V	Window mode		8.0		µA
			Comparator high-speed mode		4.0		µA
			Comparator low-speed mode		1.3		µA
LVD operating current	I_{LVD} Notes 1, 7				0.08		µA
Self-programming operating current	I_{FSP} Notes 1, 9				2.50	12.20	mA
BGO operating current	I_{BGO} Notes 1, 8				2.50	12.20	mA
SNOOZE operating current	I_{SNOZ} Note 1	ADC operation	The mode is performed Note 10		0.50	1.10	mA
			The A/D conversion operations are performed, Low voltage mode, AV_{REFP} = V_{DD} = 3.0 V		1.20	2.04	
		CSI/UART operation			0.70	1.54	
		DTC operation			3.10		

Note 1. Current flowing to V_{DD}.

Note 2. When high speed on-chip oscillator and high-speed system clock are stopped.

Note 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{RTC}, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added. I_{DD2} subsystem clock operation includes the operational current of the real-time clock.

Note 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either I_{DD1} or I_{DD2}, and I_{IT}, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, I_{FIL} should be added.

3.4 AC Characteristics

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum instruction execution time)	T_{CY}	Main system clock (f_{MAIN}) operation	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.03125		1	µs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	µs
		Subsystem clock (f_{SUB}) operation		2.4 V ≤ V_{DD} ≤ 5.5 V	28.5	30.5	31.3	µs
		In the self-programming mode	HS (high-speed main) mode	2.7 V ≤ V_{DD} ≤ 5.5 V	0.03125		1	µs
				2.4 V ≤ V_{DD} < 2.7 V	0.0625		1	µs
External system clock frequency	f_{EX}	2.7 V ≤ V_{DD} ≤ 5.5 V			1.0		20.0	MHz
		2.4 V ≤ V_{DD} ≤ 2.7 V			1.0		16.0	MHz
	f_{EXS}				32		35	kHz
External system clock input high-level width, low-level width	t_{EXH}, t_{EXL}	2.7 V ≤ V_{DD} ≤ 5.5 V			24			ns
		2.4 V ≤ V_{DD} ≤ 2.7 V			30			ns
	t_{EXHS}, t_{EXLS}				13.7			µs
TI00 to TI03, TI10 to TI13 input high-level width, low-level width	t_{TIH}, t_{TIL}				1/f_{MCK} + 10 Note			ns
Timer RJ input cycle	f_C	TRJIO		2.7 V ≤ EV_{DD0} ≤ 5.5 V	100			ns
				2.4 V ≤ EV_{DD0} < 2.7 V	300			ns
Timer RJ input high-level width, low-level width	t_{TJIH}, t_{TJIL}	TRJIO		2.7 V ≤ EV_{DD0} ≤ 5.5 V	40			ns
				2.4 V ≤ EV_{DD0} < 2.7 V	120			ns

Note The following conditions are required for low voltage interface when EV_{DD0} < V_{DD}
2.4 V ≤ EV_{DD0} < 2.7 V: MIN. 125 ns

Remark f_{MCK}: Timer array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3))

(4) During communication at same potential (simplified I²C mode)

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol	Conditions	HS (high-speed main) mode		Unit
			MIN.	MAX.	
SCLr clock frequency	f_{SCL}	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ		400 Note 1	kHz
		2.4 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ		100 Note 1	kHz
Hold time when SCLr = “L”	t_{LOW}	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		2.4V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	4600		ns
Hold time when SCLr = “H”	t_{HIGH}	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	1200		ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	4600		ns
Data setup time (reception)	$t_{SU:DAT}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	1/f_{MCK} + 220 Note 2		ns
		2.4V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	1/f_{MCK} + 580 Note 2		ns
Data hold time (transmission)	$t_{HD:DAT}$	2.7 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 50 pF, R_b = 2.7 kΩ	0	770	ns
		2.4 V ≤ EV_{DD0} ≤ 5.5 V, C_b = 100 pF, R_b = 3 kΩ	0	1420	ns

Note 1. The value must also be equal to or less than f_{MCK}/4.

Note 2. Set the f_{MCK} value to keep the hold time of SCLr = “L” and SCLr = “H”.

Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(**Remarks** are listed on the next page.)

Note 5. The smaller maximum transfer rate derived by using f_{MCK}/12 or the following expression is the valid maximum transfer rate.
Expression for calculating the transfer rate when 2.4 V ≤ EV_{DD0} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \text{ [\%]}$$

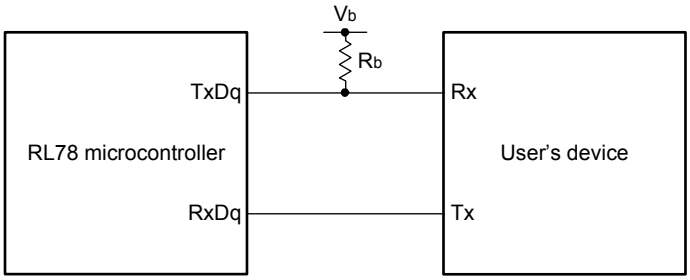
* This value is the theoretical value of the relative difference between the transmission and reception sides

Note 6. This value as an example is calculated when the conditions described in the “Conditions” column are met.
Refer to **Note 5** above to calculate the maximum transfer rate under conditions of the customer.

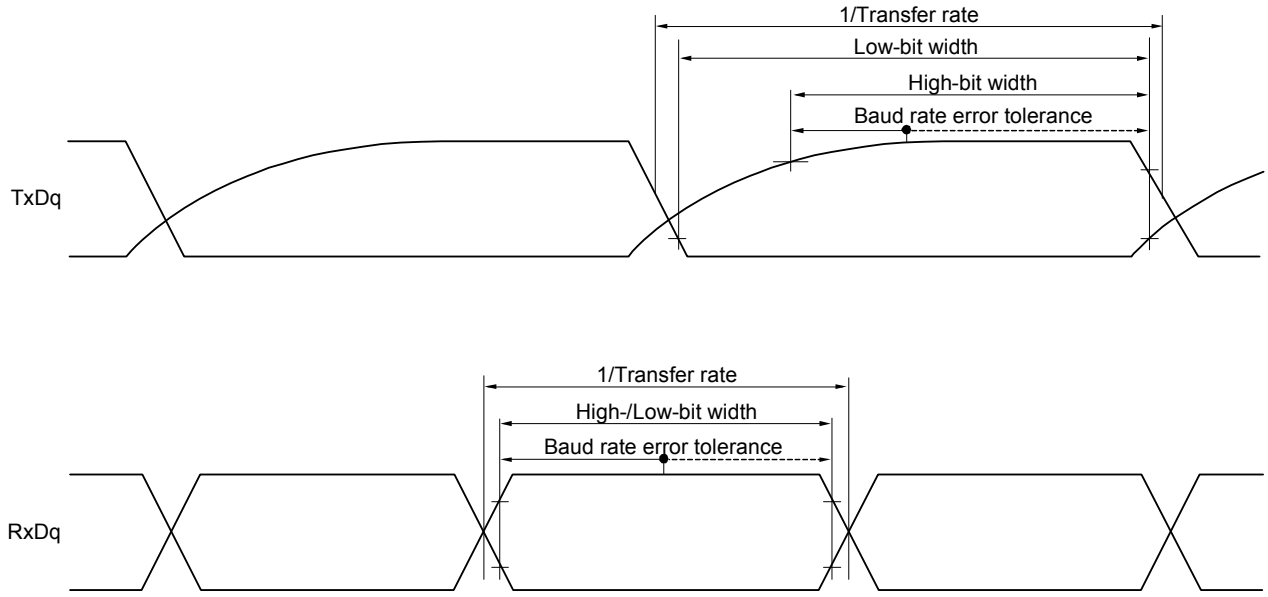
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (V_{DD} tolerance (for the 30- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For V_{IH} and V_{IL}, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed on the next page.)

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)



Remark 1. R_b[Ω]: Communication line (TxDq) pull-up resistance,
C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage

Remark 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)

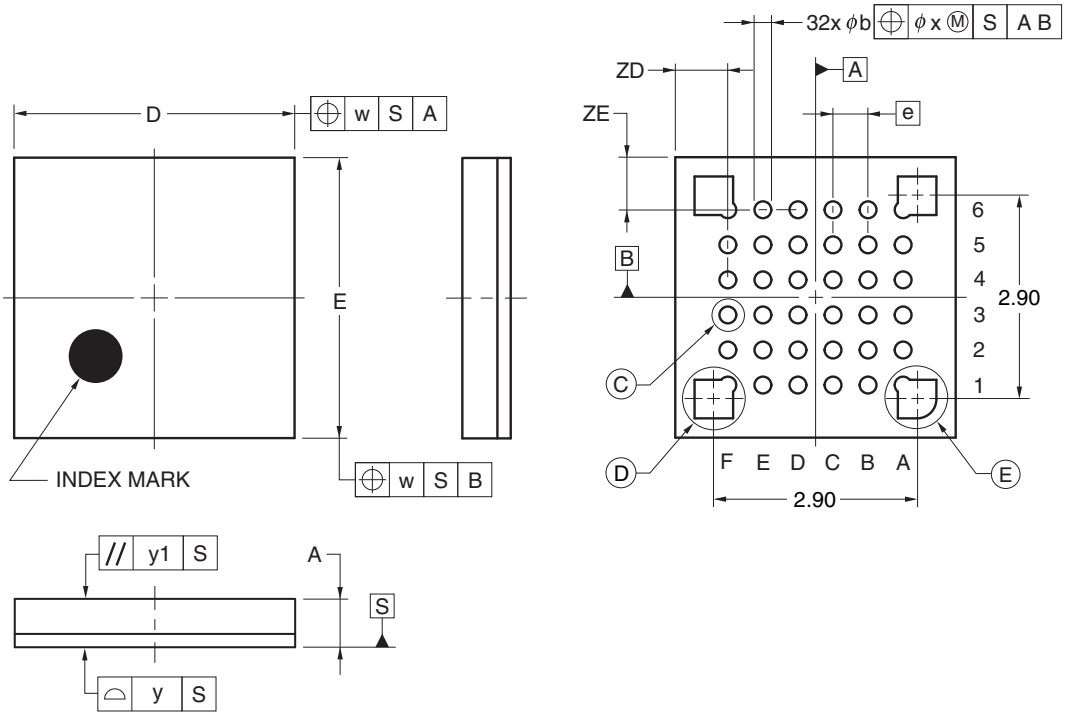
Remark 3. f_{MCK}: Serial array unit operation clock frequency
(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).
m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

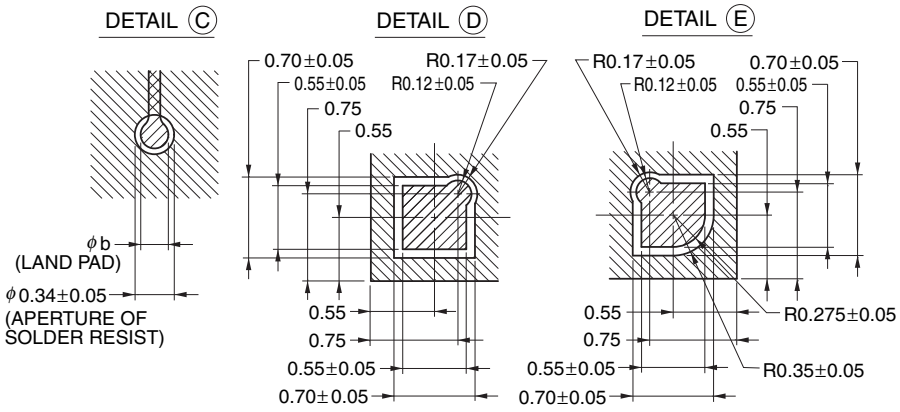
Remark 4. UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.

4.3 36-pin products

R5F104CAALA, R5F104CCALA, R5F104CDALA, R5F104CEALA, R5F104CFALA, R5F104CGALA
R5F104CAGLA, R5F104CCGLA, R5F104CDGLA, R5F104CEGLA, R5F104CFGLA, R5F104CGGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023





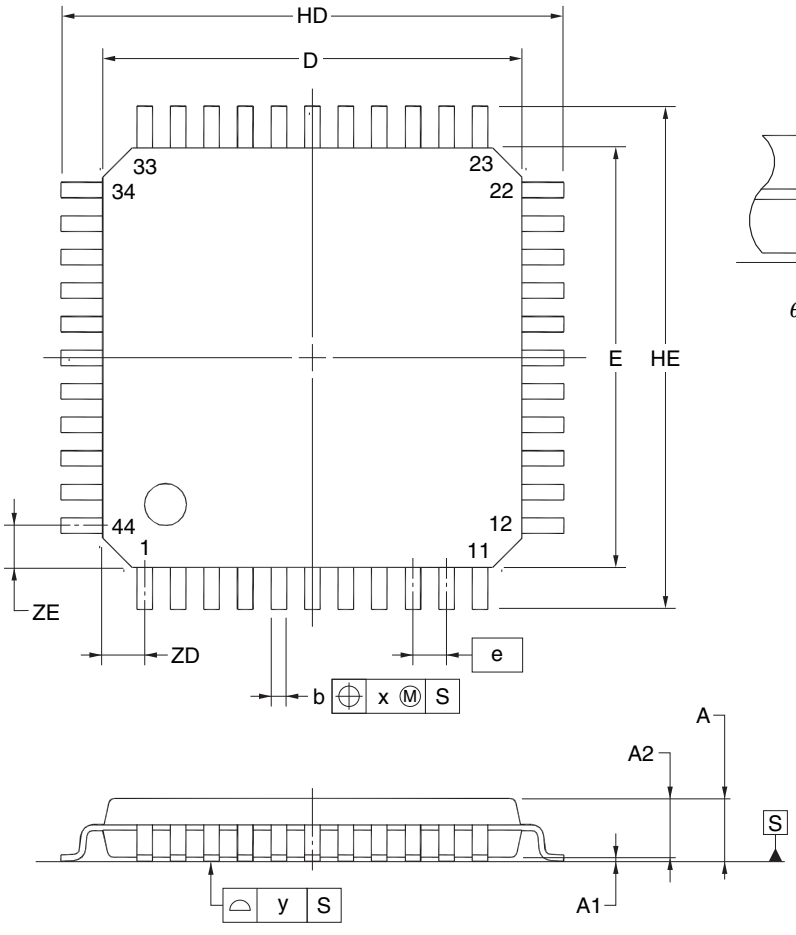
(UNIT:mm)

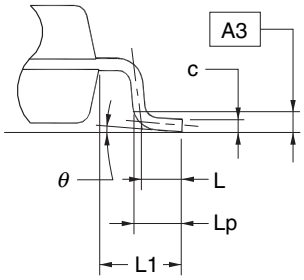
ITEM	DIMENSIONS
D	4.00±0.10
E	4.00±0.10
w	0.20
e	0.50
A	0.69±0.07
b	0.24±0.05
x	0.05
y	0.08
y1	0.20
ZD	0.75
ZE	0.75

4.5 44-pin products

R5F104FAAFP, R5F104FCAFP, R5F104FDAFP, R5F104FEAFP, R5F104FFAFP, R5F104FGAFP, R5F104FHAFP, R5F104FJAFP
R5F104FADFP, R5F104FCDFP, R5F104FDDFP, R5F104FEDFP, R5F104FFDFP, R5F104FGDFP, R5F104FHDFP, R5F104FJDFP
R5F104FAGFP, R5F104FCGFP, R5F104FDGFP, R5F104FEGFP, R5F104FFGFP, R5F104FGGFP, R5F104FHGFP, R5F104FJGFP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36





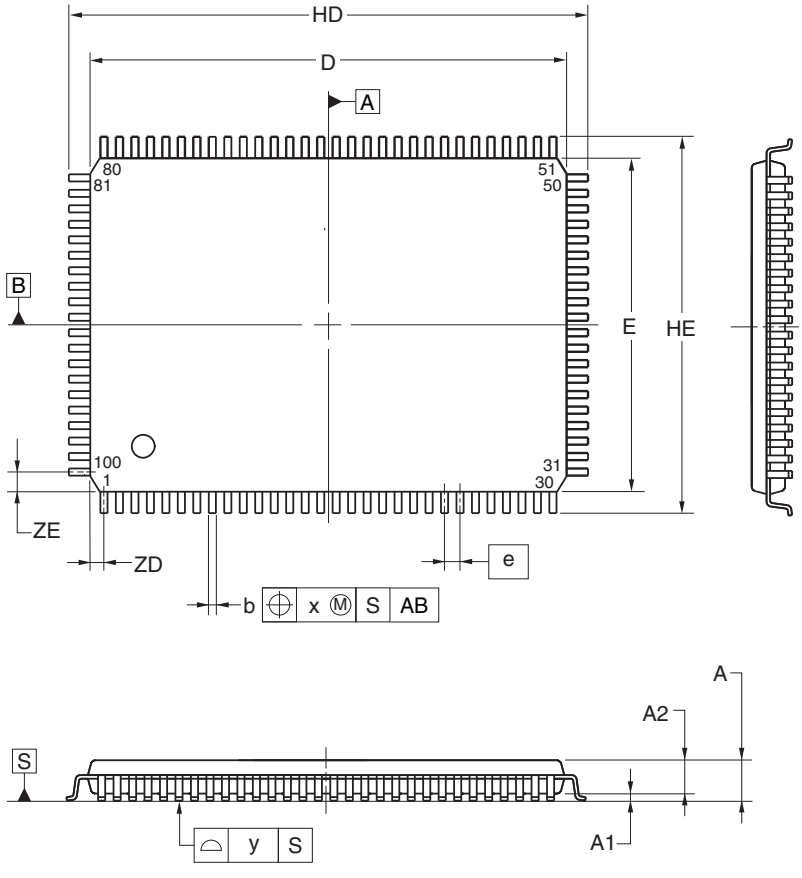
(UNIT:mm)

ITEM	DIMENSIONS
D	10.00±0.20
E	10.00±0.20
HD	12.00±0.20
HE	12.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	$0.37^{+0.08}_{-0.07}$
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
e	0.80
x	0.20
y	0.10
ZD	1.00
ZE	1.00

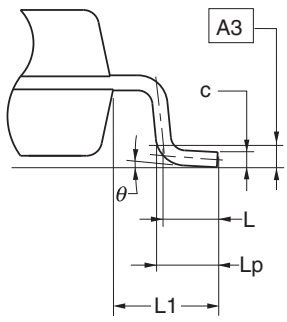
NOTE
Each lead centerline is located within 0.20 mm of its true position at maximum material condition.

R5F104PFAFA, R5F104PGAFA, R5F104PHAFA, R5F104PJAFA
R5F104PFDFA, R5F104PGDFA, R5F104PHDFA, R5F104PJDFA
R5F104PFGFA, R5F104PGGFA, R5F104PHGFA, R5F104PJGFA
R5F104PKAFA, R5F104PLAFA
R5F104PKGFA, R5F104PLGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP100-14x20-0.65	PLQP0100JC-A	P100GF-65-GBN-1	0.92



detail of lead end



(UNIT:mm)

ITEM	DIMENSIONS
D	20.00±0.20
E	14.00±0.20
HD	22.00±0.20
HE	16.00±0.20
A	1.60 MAX.
A1	0.10±0.05
A2	1.40±0.05
A3	0.25
b	$0.32^{+0.08}_{-0.07}$
c	$0.145^{+0.055}_{-0.045}$
L	0.50
Lp	0.60±0.15
L1	1.00±0.20
θ	$3^{\circ}{}^{+5^{\circ}}_{-3^{\circ}}$
e	0.65
x	0.13
y	0.10
ZD	0.575
ZE	0.825

REVISION HISTORY	RL78/G14 Datasheet

Rev.	Date	Description	
		Page	Summary
3.20	Jan 05, 2015	p.135, 137, 139, 141, 143, 145	Modification of specifications in 3.3.2 Supply current characteristics
		p.197	Modification of part number in 4.7 52-pin products
3.30	Aug 12, 2016	p.143, 145	Addition of maximum values in (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products of 3.3.2 Supply current characteristics